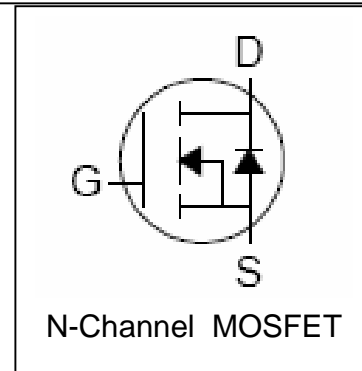
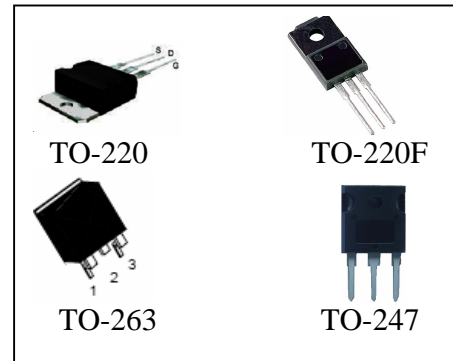


Features

- 100V/40A,
 $R_{DS(ON)} = 21m \text{ (typ.)}@V_{GS}=10V$
- Super High Dense Cell Design
- 100% avalanche tested
- Lead Free and Green Devices Available
 (RoHS Compliant)

Pin Description



Applications

- Switching application

Absolute Maximum Ratings

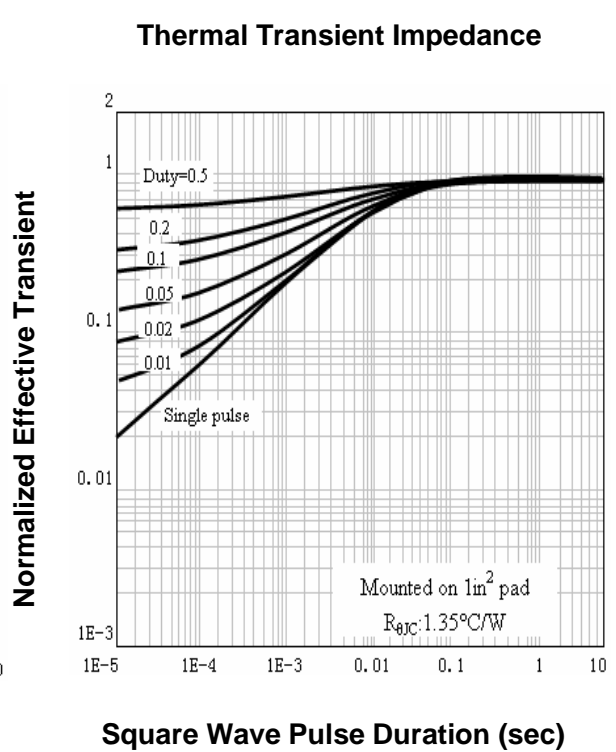
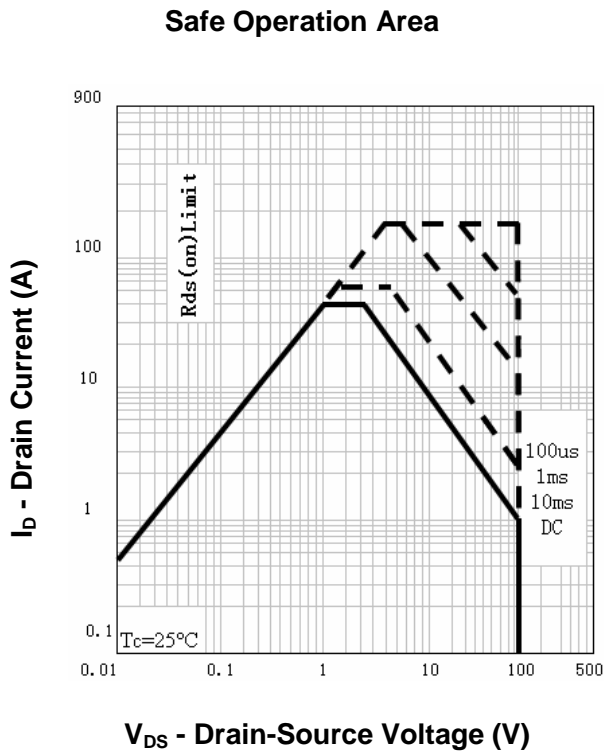
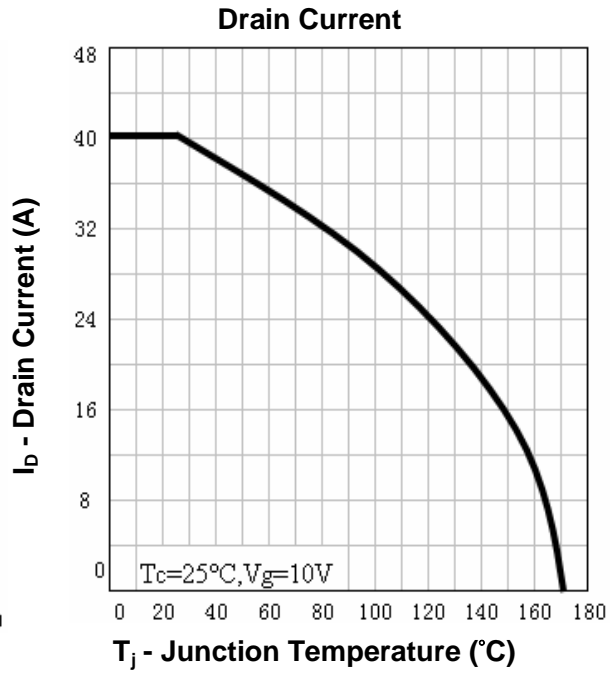
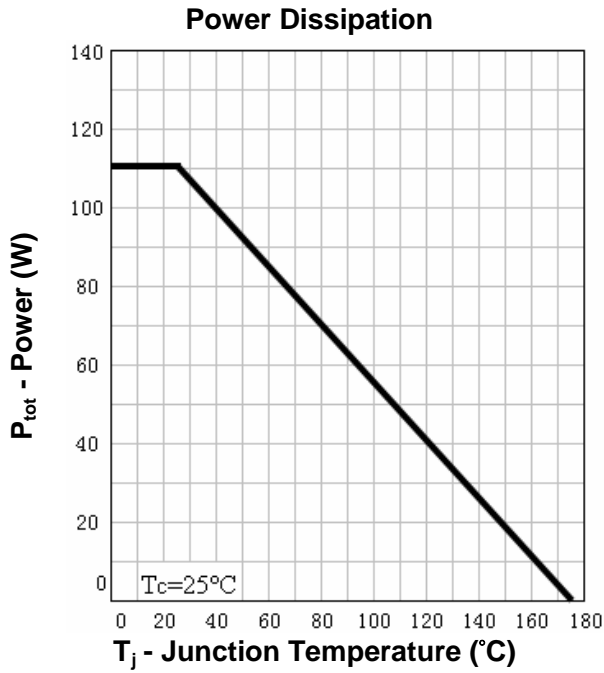
Symbol	Parameter	Rating	Unit
Common Ratings ($T_A=25^\circ\text{C}$ Unless Otherwise Noted)			
V_{DSS}	Drain-Source Voltage	100	V
V_{GSS}	Gate-Source Voltage	± 25	
T_J	Maximum Junction Temperature	175	$^\circ\text{C}$
T_{STG}	Storage Temperature Range	-55 to 175	$^\circ\text{C}$
I_S	Diode Continuous Forward Current	$T_C=25^\circ\text{C}$ 40	A
Mounted on Large Heat Sink			
I_{DP}	300 μs Pulse Drain Current Tested	$T_C=25^\circ\text{C}$ 160 ^①	A
I_D	Continuous Drain Current	$T_C=25^\circ\text{C}$ 40 ^②	A
		$T_C=100^\circ\text{C}$ 27	
P_D	Maximum Power Dissipation	$T_C=25^\circ\text{C}$ 111	W
		$T_C=100^\circ\text{C}$ 56	
$R_{\theta JC}$	Thermal Resistance-Junction to Case	1.35	$^\circ\text{C/W}$
Drain-Source Avalanche Ratings			
E_{AS} ^③	Avalanche Energy, Single Pulsed	220	mJ

Electrical Characteristics ($T_A=25^{\circ}\text{C}$ Unless Otherwise Noted)

Symbol	Parameter	Test Condition	RU1H35S			Unit
			Min.	Typ.	Max.	
Static Characteristics						
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_{DS}=250\mu A$	100			V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS}=100V, V_{GS}=0V$ $T_J=85^{\circ}\text{C}$			1	μA
					10	
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_{DS}=250\mu A$	2	3	4	V
I_{GSS}	Gate Leakage Current	$V_{GS}=\pm 25V, V_{DS}=0V$			± 100	nA
$R_{DS(ON)}^{(4)}$	Drain-Source On-state Resistance	$V_{GS}=10V, I_{DS}=16A$		21	25	m Ω
Diode Characteristics						
$V_{SD}^{(4)}$	Diode Forward Voltage	$I_{SD}=16A, V_{GS}=0V$		0.8	1.2	V
t_{rr}	Reverse Recovery Time	$I_{SD}=16A, di_{SD}/dt=100A/\mu s$		100		ns
Q_{rr}	Reverse Recovery Charge			430		nC
Dynamic Characteristics ⁽⁵⁾						
R_G	Gate Resistance	$V_{GS}=0V, V_{DS}=0V, F=1\text{MHz}$		2.8		Ω
C_{iss}	Input Capacitance	$V_{GS}=0V,$ $V_{DS}=25V,$ Frequency=1.0MHz		2100		pF
C_{oss}	Output Capacitance			250		
C_{riss}	Reverse Transfer Capacitance			115		
$t_{d(ON)}$	Turn-on Delay Time			22		
t_r	Turn-on Rise Time	$V_{DD}=50V, R_L=30\Omega,$ $I_{DS}=16A, V_{GEN}=10V,$ $R_G=4.7\Omega$		76		
$t_{d(OFF)}$	Turn-off Delay Time			60		
t_f	Turn-off Fall Time			23		
Gate Charge Characteristics ⁽⁵⁾						
Q_g	Total Gate Charge	$V_{DS}=80V, V_{GS}=10V,$ $I_{DS}=16A$		44		nC
Q_{gs}	Gate-Source Charge			10		
Q_{gd}	Gate-Drain Charge			21		

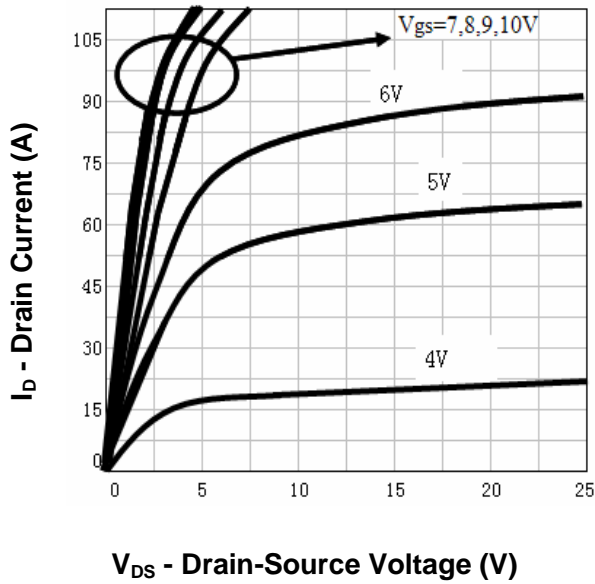
- Notes: ① Pulse width limited by safe operating area.
 ② Calculated continuous current based on maximum allowable junction temperature.
 ③ Limited by $T_{Jmax}, I_{AS}=21A, V_{DD}=48V, R_G=50\Omega$, Starting $T_J=25^{\circ}\text{C}$.
 ④ Pulse test; Pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$.
 ⑤ Guaranteed by design, not subject to production testing.

Typical Characteristics

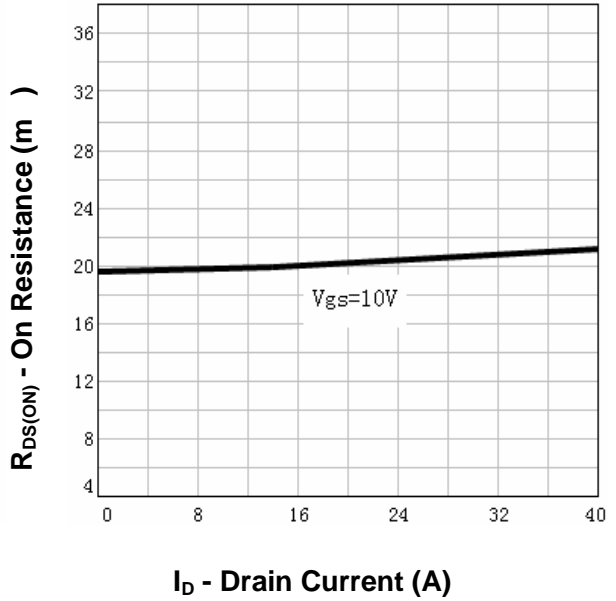


Typical Characteristics

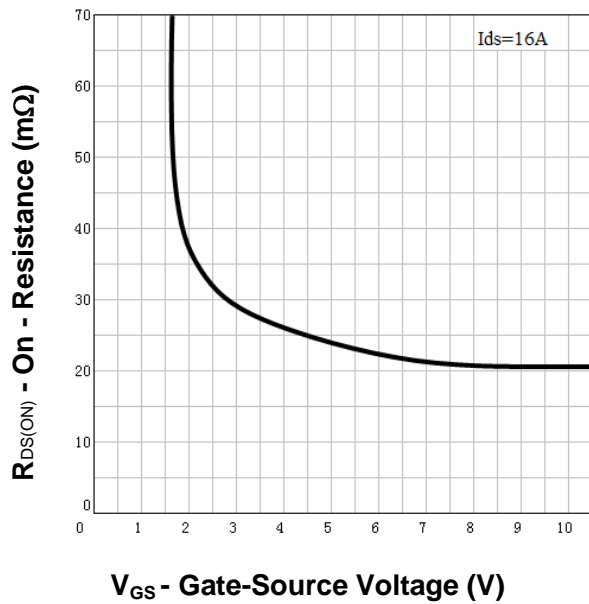
Output Characteristics



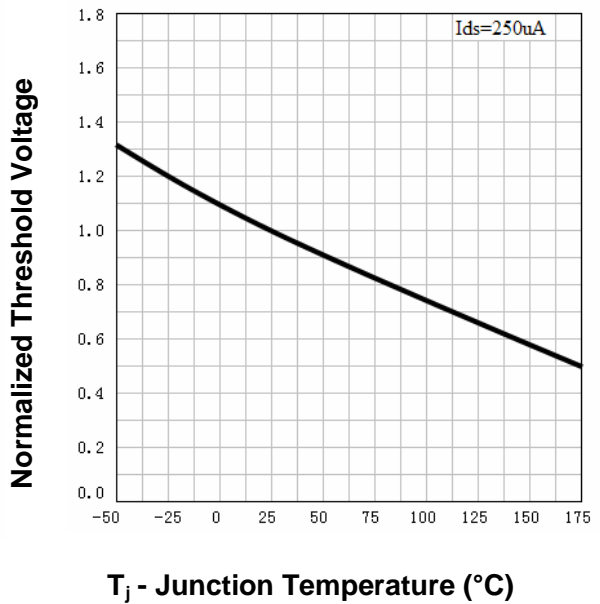
Drain-Source On Resistance



Drain-Source On Resistance

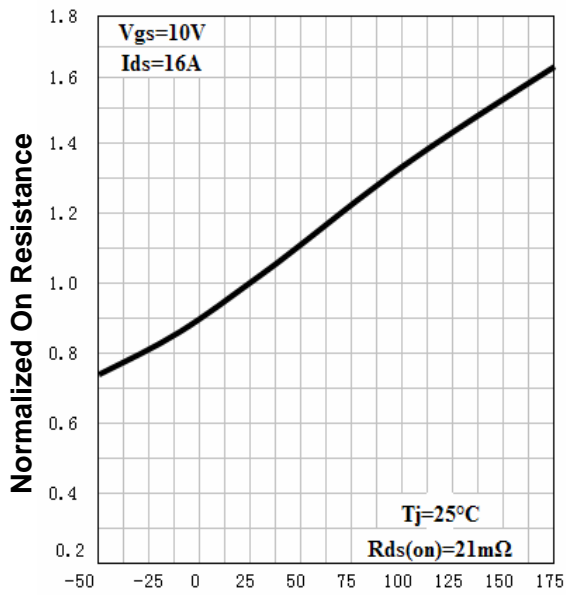


Gate Threshold Voltage



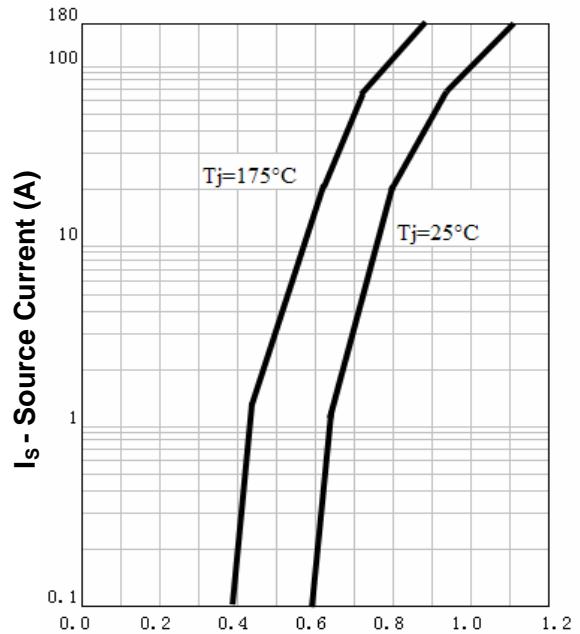
Typical Characteristics

Drain-Source On Resistance



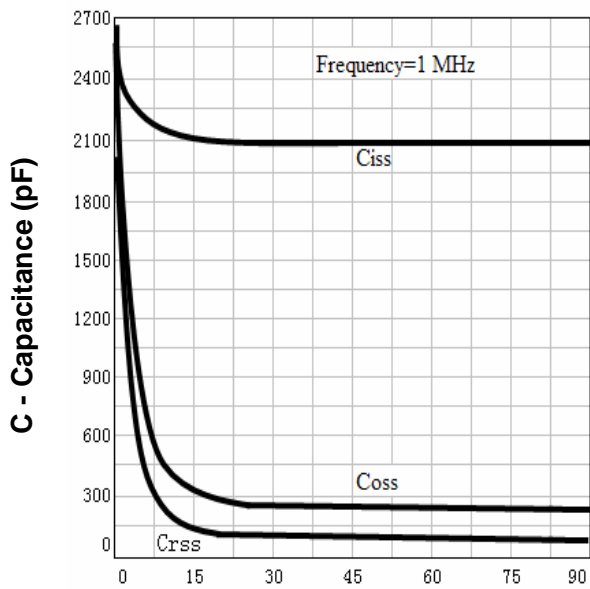
T_J - Junction Temperature (°C)

Source-Drain Diode Forward



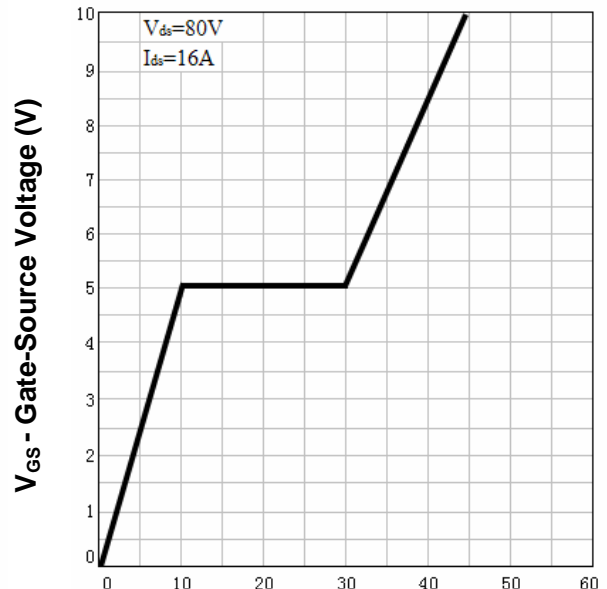
V_{SD} - Source-Drain Voltage (V)

Capacitance



V_{DS} - Drain-Source Voltage (V)

Gate Charge



Q_G - Gate Charge (nC)

Ordering and Marking Information**RU1H35****Package (Available)**

S : TO263

Operating Temperature Range

C : -55 to 175 °C

Assembly Material

G : Green & Lead Free

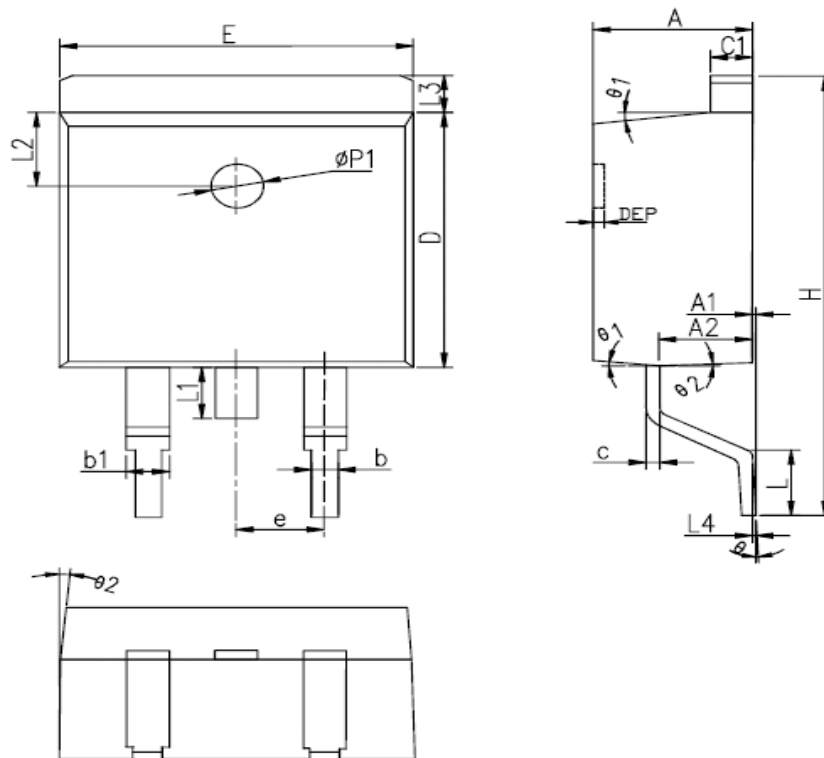
Packaging

T : TUBE

TR : Tape & Reel

Package Information

TO-263-2L



SYMBOL	MM			INCH			SYMBOL	MM			INCH		
	MIN	NOM	MAX	MIN	NOM	MAX		MIN	NOM	MAX	MIN	NOM	MAX
A	4.40	4.57	4.70	0.173	0.180	0.185	L	2.00	2.30	2.60	0.079	0.090	0.102
A1	0	0.10	0.25	0	0.004	0.010	L3	1.17	1.27	1.40	0.046	0.050	0.055
A2	2.59	2.69	2.79	0.102	0.106	0.110	L1	-	-	1.70	-	-	0.067
b	0.77	-	0.90	0.030	-	0.035	L4	0.25BSC			0.01BSC		
b1	1.23	-	1.36	0.048	-	0.052	L2	2.50REF.			0.098REF.		
c	0.34	-	0.47	0.013	-	0.019	θ	0°	-	8°	0°	-	8°
C1	1.22	-	1.32	0.048	-	0.052	θ 1	5°	7°	9°	5°	7°	9°
D	8.60	8.70	8.80	0.338	0.343	0.346	θ 2	1°	3°	5°	1°	3°	5°
E	10.00	10.16	10.26	0.394	0.4	0.404	DEP	0.05	0.10	0.20	0.002	0.004	0.008
e	2.54BSC			0.1BSC			Øp1	1.40	1.50	1.60	0.055	0.059	0.063
H	14.70	15.10	15.50	0.579	0.594	0.610							

**ALL DIMENSIONS REFER TO JEDEC STANDARD
DO NOT INCLUDE MOLD FLASH OR PROTRUSIONS**

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